



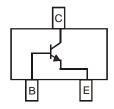
1A NPN SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- High Collector Current Rating
- Complementary Version Available (DPBT8105)
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green Device" (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)







Top View

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current - Continuous	Ic	1	А
Peak Pulse Collector Current	I _{CM}	2	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 1) @ T _A = 25°C	P_{D}	600	mW
Thermal Resistance, Junction to Ambient (Note 1) @ T _A = 25°C	$R_{ heta JA}$	209	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

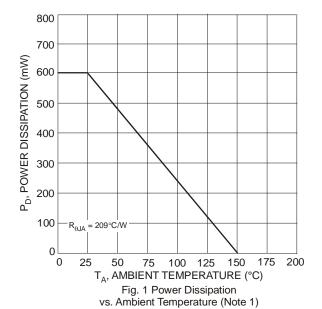
Electrical Characteristics @T_A = 25°C unless otherwise specified

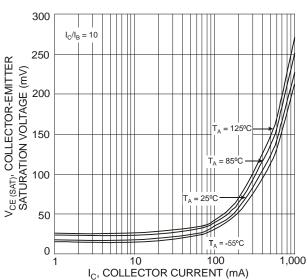
Characteristic	Symbol	Min	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)						
Collector-Base Breakdown Voltage	V _(BR) CBO	80		V	$I_C = 100 \mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	60		V	$I_C = 10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5		٧	$I_E = 100 \mu A, I_C = 0$	
Collector Cutoff Current	I _{CBO}		100	nA	$V_{CB} = 60V, I_{E} = 0$	
Collector Cutoff Current	I _{CES}		100	nA	$V_{CES} = 60V$	
Emitter Cutoff Current	I _{EBO}		100	nA	$V_{EB} = 4V, I_{C} = 0$	
ON CHARACTERISTICS (Note 4)						
DC Current Gain	h _{FE}	100 100 80 30	300 —	_	$I_C = 1mA$, $V_{CE} = 5V$ $I_C = 500mA$, $V_{CE} = 5V$ $I_C = 1A$, $V_{CE} = 5V$ $I_C = 2A$, $V_{CE} = 5V$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}		0.25 0.5	V	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$ $I_C = 1 \text{A}, I_B = 100 \text{mA}$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}		1.1	V	$I_C = 1A$, $I_B = 100mA$	
Base-Emitter Turn On Voltage	V _{BE(ON)}		1.0	V	$I_{C} = 1A, V_{CE} = 5V$	
SMALL SIGNAL CHARACTERISTICS						
Output Capacitance	C _{obo}		10	pF	$V_{CB} = 10V, f = 1.0MHz$	
Current Gain-Bandwidth Product	f _T	150		MHz	$V_{CE} = 10V, I_{C} = 50mA, f = 100MHz$	

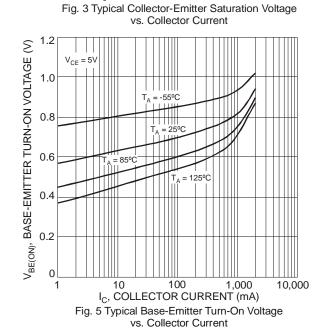
Notes:

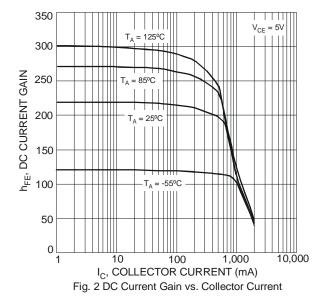
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead.
- 3. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 4. Short duration pulse test used to minimize self-heating effect.











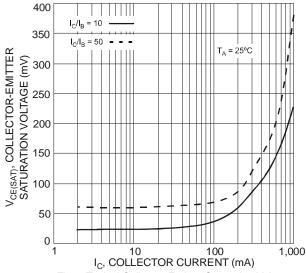


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

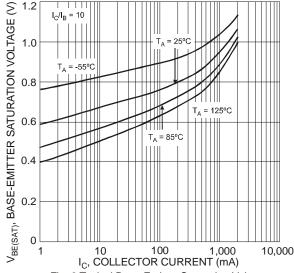
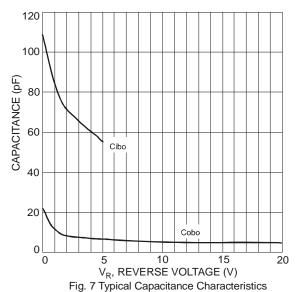


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



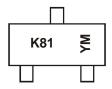


Ordering Information (Note 5)

Part Number	Case	Packaging
DNBT8105-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

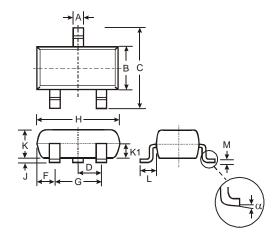


K81 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: S = 2005)

M = Month (ex: 9 = September)

Year	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015
Code	R	S	Т	U	V	W	Χ	Υ	Z	Α	В	С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

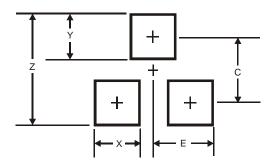
Package Outline Dimensions



SOT-23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Η	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.903	1.10	1.00				
K1	-	-	0.400				
L	0.45	0.61	0.55				
M	0.085	0.18	0.11				
α	0°	8°	-				
All Dimensions in mm							



Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	8.0
Υ	0.9
С	2.0
E	1.35

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